

제23회 한국반도체학술대회

2016년 2월 22일(월)-24일(수), 강원도 하이원리조트

K. Memory (Design & Process Technology) 분과

Room J

청옥 I (6층)

2016년 2월 23일(화) 10:40-12:40

[TJ2-K] NAND, PCRAM, and MRAM

좌장 : 강명곤(한국교통대학교), 이재구(삼성전자)

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| TJ2-K-1 | 10:40-10:55 | Investigation of Retention Characteristics in NAND Flash Memory
Kyunghwan Lee ¹ , Myounggon Kang ² , and Hyungcheol Shin ¹
<i>¹Department of Electrical and Computer Engineering and Inter-university Semiconductor Research Center, Seoul National University, ²Department of Electrical Engineering, Korea National University of Transportation</i> |
| TJ2-K-2 | 10:55-11:10 | Threshold Voltage Setting Method for Layer Selection by Multi-Level Operation in Channel Stacked NAND Flash memory with Body
Do-Bin Kim, Dae Woong Kwon, Wandong Kim, and Byung-Gook Park
<i>Inter-university Semiconductor Research Center and the Department of Electrical and Computer Engineering, Seoul National University</i> |
| TJ2-K-3 | 11:10-11:25 | Self-Structured Nanofilament Induced Heating for Ultra-Low Power Operations of Phase-Change Memory
Byoung Kuk You and Keon Jae Lee
<i>Department of Materials Science and Engineering, KAIST</i> |
| TJ2-K-4 | 11:25-11:40 | Improvement on Operation Speed of In₃SbTe₂ Phase-change Material by Bi Doping
Minho Choi ¹ , Heechae Choi ² , Seungchul Kim ² , Yong Tae Kim ³ , and Jinho Ahn ¹
<i>¹Department of Materials Science and Engineering, Hanyang University, ²Center for Computational Science, Korea Institute of Science and Technology, ³Semiconductor Laboratory, Korea Institute of Science and Technology</i> |
| TJ2-K-5 | 11:40-11:55 | Formation of Ge-Sb-Te Thin Film by Tellurization of Ge-Sb Film
Yu-Jin Kim ¹ , Byeol Han ¹ , Jae-Min Park ¹ , Mann-Ho Cho ² , and Won-Jun Lee ¹
<i>¹Department of Nanotechnology and Advanced Materials Engineering, Sejong University, ²Institute of Physics and Applied Physics, Yonsei University</i> |
| TJ2-K-7 | 12:10-12:25 | A Study on the Electrical Damage Control of Noble MRAM Device using Plasma Etching Process
Jaehun Seo, Jongkyu Kim, Jungik Oh, Jongchul Park, Kyungsub Chin, Seokwoo Nam, Hokyu Kang, and ES Jung
<i>Process development Team, Semiconductor R&D Center, Samsung</i> |

The 23rd Korean Conference on Semiconductors (KCS 2016)

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Electrics Co., Ltd.

TJ2-K-8 12:25-12:40 A Study on the Surface Treatment of MTJ Material for MRAM Device using Oxygen Ion Beam Etching
Sang-Kuk Kim, Jong-kyu Kim, Jong-Soon Park, Jong-chul Park, Kyung-sub Shin, Seok-Woo Nam, Ho-Kyu Kang, and ES Jung
Process Development 1 Team, Semiconductor R&D Center, Samsung Electronics Co., Ltd.